
HZM6.8FA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-442A(Z)

Rev 1

September 1996

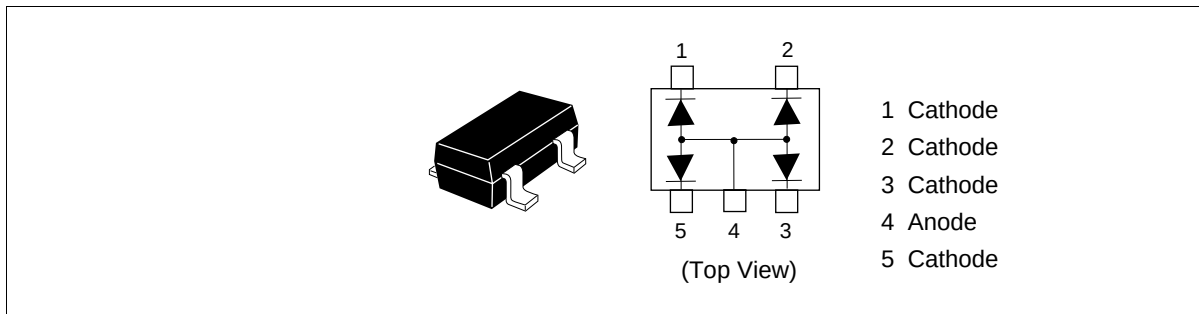
Features

- HZM6.8FA has four devices, and can absorb external + and -surge.
- MPAK-5 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM6.8FA	68A	MPAK-5

Outline



HZM6.8FA

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd *1	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note 1. Four device total, With P.C board.

Electrical Characteristics (Ta = 25°C) *1

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	VZ	6.47	Å\	7.0	V	IZ = 5 mA, 40ms pulse
Reverse current	IR	Å\	Å\	2	µA	VR = 3.5V
Capacitance	C	Å\	Å\	130	pF	VR = 0V, f = 1 MHz
Dynamic resistance	r d	Å\	Å\	30	Ω	IZ = 5 mA
ESD-Capability	Å\	30	Å\	Å\	kV	C =150pF, R = 330 Ω, Both forward and reverse direction 10 pulse *2

Notes 1. Per one device.

2. Failure criterion ; IRÅÑ2 µA at VR = 3.5V.

Main Characteristic

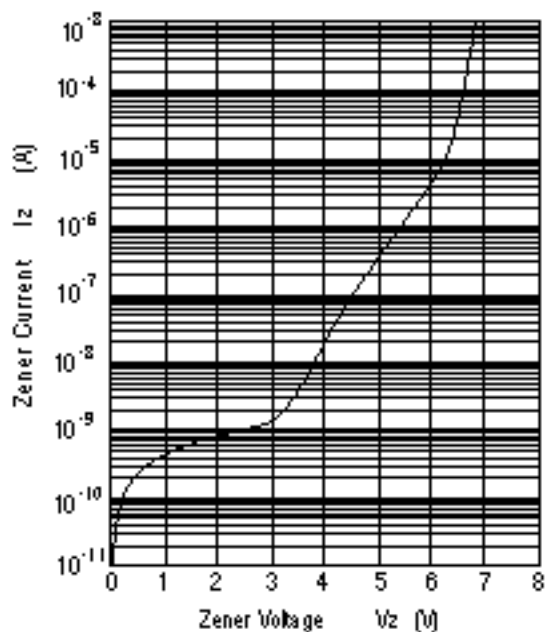


Fig.1 Zener current Vs. Zener voltage

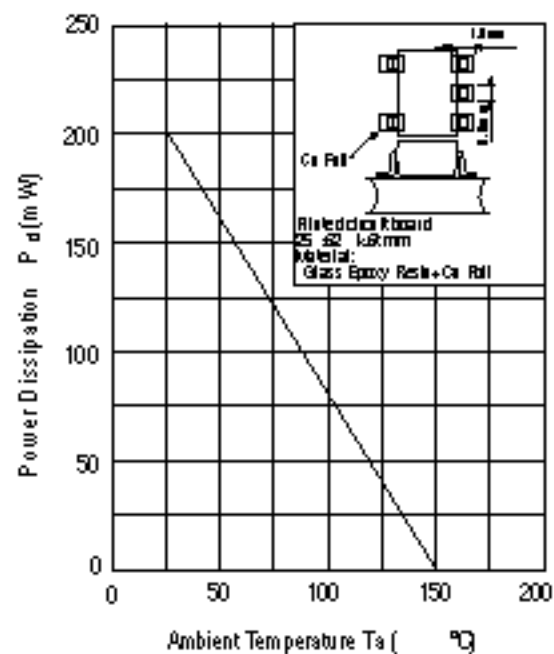


Fig.2 Power Dissipation Vs. Ambient Temperature

HZM6.8FA

Package Dimensions

Unit : mm

